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33. (Amended) A process for depositing a tungsten silicide film on a substrate consisting essentially of:  
depositing a discontinuous nucleation layer of tungsten silicide (WSi<sub>x</sub>) on the substrate using a (CVD) process with a silane (SiH<sub>4</sub>) silicon source gas and a reactant gas;  
depositing a film of tungsten silicide (WSi<sub>x</sub>) on the discontinuous nucleation layer using a (CVD) process by switching to dichlorosilane (SiH<sub>2</sub>Cl<sub>2</sub>) as a silicon source gas such that the dichlorosilane gas reacts with the reactant gas to form the tungsten silicide film; and  
wherein said depositing said discontinuous nucleation layer of tungsten silicide and said depositing said film of tungsten silicide occur at a substantially equivalent temperature.

**REMARKS**

No new matter has been added. The Applicant requests entry of the foregoing amendment prior to examination of the application on the merits.

Respectfully submitted,



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